

Application of: Euijoon Yoon et al.
Serial No.: 10/596,126
Amendment after Non-Final Office Action

AMENDMENTS TO THE ABSTRACT

Please replace the original Abstract with the following paragraph:

[Abstract]

~~The present invention relates to a growth method of nitride semiconductor layer~~
comprising a first step for growing Growing a first nitride $[[5]]$ semiconductor layer on an
 ~~$Al_xGa_yIn_{1-x-y}N(0 < x < 1, 0 < y < 1, 0 < x+y < 1)$~~ $Al_xGa_yIn_{1-x-y}N(0 \leq x \leq 1, 0 \leq y \leq 1, 0 < x+y \leq 1)$ layer, a
second step for reducing the thickness of the first nitride semiconductor layer by growth
interruption and, a third step for growing a second nitride semiconductor layer having a band gap
energy higher than that of the first nitride semiconductor layer on the first nitride semiconductor
layer with the $[[to]]$ reduced thickness and a light emitting device using the growth method.